

High-density chain ferroelectric random access memory

IEEE Journal of Solid-State Circuits

33, 787-792

DOI: 10.1109/4.668994

Citation Report

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 1 | Tunnelling-based SRAM. Nanotechnology, 1999, 10, 174-186. | 2.6 | 34 |
| 2 | A sub-40 ns random-access chain FRAM architecture with a 768 cell-plate-line drive. , 0, , . | | 4 |
| 3 | A sub-40-ns chain FRAM architecture with 7-ns cell-plate-line drive. IEEE Journal of Solid-State Circuits, 1999, 34, 1557-1563. | 5.4 | 12 |
| 4 | Tunneling-based SRAM. Proceedings of the IEEE, 1999, 87, 571-595. | 21.3 | 116 |
| 5 | Degradation of Ferroelectric Capacitors during Metal Etching and Ashing Processes. Materials Research Society Symposia Proceedings, 2000, 655, 284. | 0.1 | 0 |
| 6 | A 3.3-V, 4-Mb nonvolatile ferroelectric RAM with selectively driven double-pulsed plate read/write-back scheme. IEEE Journal of Solid-State Circuits, 2000, 35, 697-704. | 5.4 | 18 |
| 7 | A survey of circuit innovations in ferroelectric random-access memories. Proceedings of the IEEE, 2000, 88, 667-689. | 21.3 | 181 |
| 8 | A 76-mm/sup 2/ 8-Mb chain ferroelectric memory. IEEE Journal of Solid-State Circuits, 2001, 36, 1713-1720. | 5.4 | 28 |
| 9 | Comparison between standard and chain-type FRAM architectures. Integrated Ferroelectrics, 2001, 34, 1-10. | 0.7 | 0 |
| 10 | A 76 mm/sup 2/ 8 Mb chain ferroelectric memory. , 0, , . | | 0 |
| 11 | Advanced simulation tool for FeRAM design. Integrated Ferroelectrics, 2001, 40, 101-112. | 0.7 | 6 |
| 12 | RECENT PROGRESS OF FERROELECTRIC MEMORIES. International Journal of High Speed Electronics and Systems, 2002, 12, 315-323. | 0.7 | 5 |
| 13 | A new working principle of ferroelectric gate FET memory with an additional electrode. , 0, , . | | 0 |
| 14 | Low thermal-budget process of sputtered-PZT capacitor over multilevel metallization. IEEE Transactions on Electron Devices, 2003, 50, 2081-2087. | 3.0 | 11 |
| 15 | Emerging non-volatile memory technologies. , 0, , . | | 9 |
| 16 | A 32-Mb chain FeRAM with segment/stitch array architecture. IEEE Journal of Solid-State Circuits, 2003, 38, 1911-1919. | 5.4 | 12 |
| 17 | Retention and Read Endurance Characteristics of a Ferroelectric Gate Field Effect Transistor Memory with an Intermediate Electrode. Japanese Journal of Applied Physics, 2004, 43, 2220-2225. | 1.5 | 6 |
| 18 | Complementary ferroelectric-capacitor logic for low-power logic-in-memory VLSI. IEEE Journal of Solid-State Circuits, 2004, 39, 919-926. | 5.4 | 55 |

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 19 | PZT MIM Capacitor With Oxygen-Doped Ru-Electrodes for Embedded FeRAM Devices. IEEE Transactions on Electron Devices, 2005, 52, 2227-2235. | 3.0 | 17 |
| 20 | 0.18- μm Nondestructive Readout FeRAM Using Charge Compensation Technique. IEEE Transactions on Electron Devices, 2005, 52, 2616-2621. | 3.0 | 21 |
| 21 | A NEW HIGH-RELIABLE 2T/1C FeRAM CELL. Integrated Ferroelectrics, 2006, 81, 149-155. | 0.7 | 0 |
| 22 | A SrRuO ₃ /IrO ₂ top electrode FeRAM with Cu BEOL process for embedded memory of 130nm generation and beyond. Solid-State Electronics, 2006, 50, 606-612. | 1.4 | 17 |
| 23 | Key process technology for high density 64M FeRAM and beyond. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , . | 0.0 | 0 |
| 24 | Overview of candidate device technologies for storage-class memory. IBM Journal of Research and Development, 2008, 52, 449-464. | 3.1 | 588 |
| 25 | A 128Mb ChainFeRAM TM and system designs for HDD application and enhanced HDD performance. , 2009, , . | | 3 |
| 26 | Ferroelectric Field Effect Transistors for Memory Applications. Advanced Materials, 2010, 22, 2957-2961. | 21.0 | 257 |
| 27 | Overview and Technical Trend of Chain FeRAM. Materials Research Society Symposia Proceedings, 2010, 1250, 1. | 0.1 | 2 |
| 28 | A 64-Mb Chain FeRAM With Quad BL Architecture and 200 MB/s Burst Mode. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2010, 18, 1745-1752. | 3.1 | 19 |
| 29 | A 1.6 GB/s DDR2 128 Mb Chain FeRAM With Scalable Octal Bitline and Sensing Schemes. IEEE Journal of Solid-State Circuits, 2010, 45, 142-152. | 5.4 | 54 |
| 30 | A scalable shield-bitline-overdrive technique for 1.3V Chain FeRAM. , 2010, , . | | 9 |
| 31 | Highly reliable reference bitline bias designs for 64Mb and 128Mb chain FeRAMs. , 2010, , . | | 0 |
| 32 | A 100MHz ladder FeRAM design with capacitance-coupled-bitline (CCB) cell. , 2010, , . | | 2 |
| 33 | Overview of FeRAMs: Trends and perspectives. , 2011, , . | | 19 |
| 34 | A 128 Mb Chain FeRAM and System Design for HDD Application and Enhanced HDD Performance. IEEE Journal of Solid-State Circuits, 2011, 46, 530-536. | 5.4 | 18 |
| 35 | A 100 MHz Ladder FeRAM Design With Capacitance-Coupled-Bitline (CCB) Cell. IEEE Journal of Solid-State Circuits, 2011, 46, 681-689. | 5.4 | 17 |
| 36 | A Scalable Shield-Bitline-Overdrive Technique for Sub-1.5 V Chain FeRAMs. IEEE Journal of Solid-State Circuits, 2011, 46, 2171-2179. | 5.4 | 2 |

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 37 | State-of-the-art flash memory devices and post-flash emerging memories. Science China Information Sciences, 2011, 54, 1039-1060. | 4.3 | 5 |
| 38 | Phase Change Memory: From Devices to Systems. Synthesis Lectures on Computer Architecture, 2011, 6, 1-134. | 1.3 | 52 |
| 39 | Future Prospect of Nanoelectronic Devices. Lecture Notes in Electrical Engineering, 2013, , 171-279. | 0.4 | 1 |
| 40 | Design Technology of Stacked- ϵ -Type Chain PRAM. Electronics and Communications in Japan, 2015, 98, 32-42. | 0.5 | 0 |
| 41 | Highly Reliable Reference Bitline Bias Designs for 64 Mb and 128 Mb Chain FeRAMs. IEEE Journal of Solid-State Circuits, 2015, 50, 1324-1331. | 5.4 | 4 |
| 42 | Current-voltage hysteresis of the composite MoS ₂ -MoO ₃ nanobelts for data storage. Journal of Alloys and Compounds, 2016, 679, 47-53. | 5.5 | 19 |
| 43 | Bi _{3.25} La _{0.75} Ti _{2.5} Nb _{0.25} (Fe _{0.5} Co _{0.5}) _{0.25} a single phase room temperature multiferroic. Journal of Materials Chemistry C, 2018, 6, 2733-2740. | 5.5 | 19 |
| 44 | Stable and switchable electric polarization in two dimensions. Nature, 2018, 560, 174-175. | 27.8 | 20 |
| 45 | Switching behavior of resistive change memory using oxide nanowires. Japanese Journal of Applied Physics, 2018, 57, 06HD07. | 1.5 | 1 |
| 46 | Sensing in Ferroelectric Memories and Flip-Flops. , 2019, , 47-80. | | 0 |
| 47 | Ferroelectric memories. , 2019, , 393-441. | | 10 |
| 48 | Multiferroic properties of aurivillius structure Bi ₄ SmFeTi ₃ O ₁₅ thin films. Journal of Materials Science: Materials in Electronics, 2019, 30, 9945-9954. | 2.2 | 7 |
| 49 | Controllable Functional Layer and Temperature-Dependent Characteristic in Niobium Oxide Insulator-Metal Transition Selector. IEEE Transactions on Electron Devices, 2020, 67, 2771-2777. | 3.0 | 13 |
| 50 | CMOS-Compatible Fabrication of Low-Power Ferroelectric Tunnel Junction for Neural Network Applications. IEEE Transactions on Electron Devices, 2021, 68, 879-884. | 3.0 | 27 |
| 51 | FeRAM. Integrated Circuits and Systems, 2009, , 279-328. | 0.2 | 6 |
| 52 | FeRAM. , 2014, , 149-171. | | 2 |
| 53 | Overview and Scaling Prospect of Ferroelectric Memories. , 2010, , 361-380. | | 3 |
| 54 | Flash Memories: An Overview. , 1999, , 1-35. | | 1 |

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 55 | Revival of Ferroelectric Memories Based on Emerging Fluorite-Structured Ferroelectrics. <i>Advanced Materials</i> , 2023, 35, . | 21.0 | 23 |
| 56 | Ferroelectric Memory. , 2023, , 218-240. | | 0 |
| 57 | Memory devices—Non-volatile memories. , 2024, , 552-575. | | 0 |
| 58 | Improved Resistive and Synaptic Characteristics in Neuromorphic Systems Achieved Using the Double-Forming Process. <i>Nanomaterials</i> , 2023, 13, 2859. | 4.1 | 0 |